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Vishay Semiconductor/Diodes Division VESD01-02V-G-08

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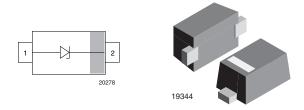


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VESDxx-02V

Vishay Semiconductors

# Single ESD-Protection Diode in SOD-523



#### MARKING (example only)



Bar = cathode marking

X = date code

Y = type code (see table below)

#### FEATURES

- Single-line ESD-protection
- Low leakage current
- ESD-immunity acc. IEC 61000-4-2 ± 8 kV contact discharge ± 15 kV air discharge
- e3 Sn

 Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>



<u>GREEN</u>

<u>(5-2008)</u>

Document Number: 83367

ORDERING INFORMATION						
DEVICE NAME	ORDERING CODE	TAPED UNITS PER REEL (8 mm TAPE ON 7" REEL)	MINIMUM ORDER QUANTITY			
VESD01-02V	VESD01-02V-G-08	3000	3000			
VESD03-02V	VESD03-02V-G-08	3000	3000			
VESD05-02V	VESD05-02V-G-08	3000	3000			
VESD08-02V	VESD08-02V-G-08	3000	3000			
VESD12-02V	VESD12-02V-G-08	3000	3000			

PACKAGE DATA									
DEVICE NAME	PACKAGE NAME	TYPE CODE	WEIGHT	MOLDING COMPOUND FLAMMABILITY RATING	MOISTURE SENSITIVITY LEVEL	SOLDERING CONDITIONS			
VESD01-02V	SOD-523	. <b>∀</b>	1.4 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals			
VESD03-02V	SOD-523	. В	1.4 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals			
VESD05-02V	SOD-523	. O	1.4 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals			
VESD08-02V	SOD-523	D.	1.4 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals			
VESD12-02V	SOD-523	Ε.	1.4 mg	UL 94 V-0	MSL level 1 (according J-STD-020)	260 °C/10 s at terminals			

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ABSOLUTE MAXIMU	RATINGS VESD01-02V			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I <sub>PPM</sub>	7	А
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P <sub>PP</sub>	63	W
	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	63 ± 8	kV
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 15	kV
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C
Storage temperature		T <sub>stg</sub>	- 55 to + 150	°C

ABSOLUTE MAXIMU	M RATINGS VESD03-02V			
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I <sub>PPM</sub>	9	А
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P <sub>PP</sub>	108	W
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	108 ± 8	kV
ESD initiality	Air discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 15	kV
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C
Storage temperature		T <sub>stg</sub>	- 55 to + 150	°C

ABSOLUTE MAXIMUM RATINGS VESD05-02V						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I <sub>PPM</sub>	6	A		
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P <sub>PP</sub>	120	W		
	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	120 ± 8	kV		
ESD immunity	Air discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 15	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C		
Storage temperature		T <sub>stg</sub>	- 55 to + 150	°C		

ABSOLUTE MAXIMUN	E MAXIMUM RATINGS VESD08-02V					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I <sub>PPM</sub>	4	A		
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P <sub>PP</sub>	120	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	M	120 ± 8	kV		
ESD Initiality	Air discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 15	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C		
Storage temperature		T <sub>stg</sub>	- 55 to + 150	°C		

ABSOLUTE MAXIMUM RATINGS VESD12-02V						
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT		
Peak pulse current	Acc. IEC 61000-4-5, 8/20 µs/single shot	I <sub>PPM</sub>	2	А		
Peak pulse power	Acc. IEC 61000-4-5, 8/20 µs/single shot	P <sub>PP</sub>	25	W		
ESD immunity	Contact discharge acc. IEC 61000-4-2; 10 pulses	V	25 ± 8	kV		
ESD minumity	Air discharge acc. IEC 61000-4-2; 10 pulses	V <sub>ESD</sub>	± 15	kV		
Operating temperature	Junction temperature	TJ	- 40 to + 125	°C		
Storage temperature		T <sub>stg</sub>	- 55 to + 150	°C		





Datasheet of VESD01-02V-G-08 - TVS DIODE 1VWM 9VC SOD523 Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com

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ELECTRICAL CHARAC	TERISTICS VESD01-02V					
$(T_{amb} = 25 \degree C, unless otherwise)$	erwise specified)					
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V <sub>RWM</sub>	-	-	1	V
Reverse voltage	at I <sub>R</sub> = 100 μA	V <sub>R</sub>	1	-	-	V
Reverse current	at V <sub>R</sub> = 1 V	I <sub>R</sub>	-	-	100	μA
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	V <sub>BR</sub>	1.5	-	-	V
Reverse clamping voltage	at I <sub>PP</sub> (see fig. 1)	V <sub>C</sub>	-	9	-	V
Capacitance	at $V_R = 0 V$ ; f = 1 MHz	CD	-	180	-	pF

<b>ELECTRICAL CHARAC</b> (T <sub>amb</sub> = 25 °C, unless othe						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V <sub>RWM</sub>	-	-	3	V
Reverse voltage	at I <sub>R</sub> = 20 μA	V <sub>R</sub>	3	-	-	V
Reverse current	at V <sub>R</sub> = 3 V	I <sub>R</sub>	-	-	20	μA
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	V <sub>BR</sub>	4	-	-	V
Reverse clamping voltage	at I <sub>PP</sub> (see fig. 1)	V <sub>C</sub>	-	12	-	V
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	CD	-	110	-	pF

ELECTRICAL CHARAC (T <sub>amb</sub> = 25 °C, unless othe	TERISTICS VESD05-02V erwise specified)					
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V <sub>RWM</sub>	-	-	5	V
Reverse voltage	at I <sub>R</sub> = 0.1 µA	V <sub>R</sub>	5	-	-	V
Reverse current	at V <sub>R</sub> = 5 V	I <sub>R</sub>	-	-	0.1	μA
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	V <sub>BR</sub>	6.5	-	-	V
Reverse clamping voltage	at I <sub>PP</sub> (see fig. 1)	V <sub>C</sub>	-	20	-	V
Capacitance	at $V_R = 0 V$ ; f = 1 MHz	CD	-	55	-	pF

ELECTRICAL CHARACT (T <sub>amb</sub> = 25 °C, unless othe						
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V <sub>RWM</sub>	-	-	8	V
Reverse voltage	at I <sub>R</sub> = 0.1 μA	V <sub>R</sub>	8	-	-	V
Reverse current	at V <sub>R</sub> = 8 V	I <sub>R</sub>	-	-	0.1	μA
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	V <sub>BR</sub>	9	-	-	V
Reverse clamping voltage	at I <sub>PP</sub> (see fig. 1)	V <sub>C</sub>	-	30	-	V
Capacitance	at V <sub>R</sub> = 0 V; f = 1 MHz	CD	-	35	-	pF

<b>ELECTRICAL CHARAC</b> $(T_{amb} = 25 \text{ °C}, \text{ unless otherwise})$	TERISTICS VESD12-02V erwise specified)					
PARAMETER	TEST CONDITIONS/REMARKS	SYMBOL	MIN.	TYP.	MAX.	UNIT
Protection paths	Number of lines which can be protected	N <sub>channel</sub>	-	-	1	lines
Reverse stand-off voltage	Max. reverse working voltage	V <sub>RWM</sub>	-	-	12	V
Reverse voltage	at I <sub>R</sub> = 0.1 μA	V <sub>R</sub>	12	-	-	V
Reverse current	at V <sub>R</sub> = 12 V	I <sub>R</sub>	-	-	0.1	μA
Reverse breakdown voltage	at I <sub>R</sub> = 1 mA	V <sub>BR</sub>	14	-	-	V
Reverse clamping voltage	at I <sub>PP</sub> (see fig. 1)	V <sub>C</sub>	-	25	-	V
Capacitance	at $V_R = 0 V$ ; f = 1 MHz	CD	-	30	-	pF

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For technical questions, contact: ESDprotection@vishay.com

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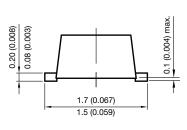


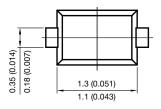
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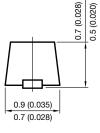
#### VESDxx-02V

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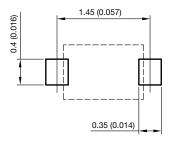
PACKAGE DIMENSIONS in millimeters (Inches): SOD-523











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